

AMENDMENTS TO ABSTRACT

A method of fabricating a thin film transistor TFT (TFT) array discloses ~~ions of desired-plated metal and the graphs of the desired-plated area are made~~ involves ion replacement by oxidation-reduction ~~materials processes ion replacement~~ for implementing the metal wiring layout of the TFT-LCDs. This ~~[[,]] therefore, can overcome the problem of uneasy metal etching thereto achieves the purpose of an~~ difficulties and achieve automatic alignment. ~~The method uses the ability of the oxidation-reduction reaction to implement the replacement for alternating the lithography etching process in the metal wiring layout as presented in the traditional technique~~ The method of the invention replaces traditional lithographic etching techniques.